



UT2301

Power MOSFET

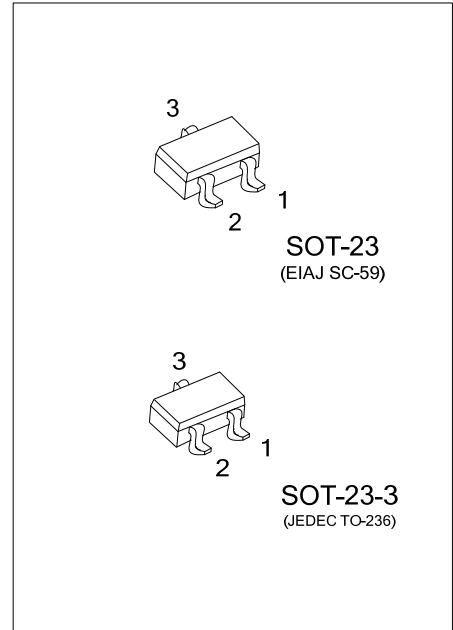
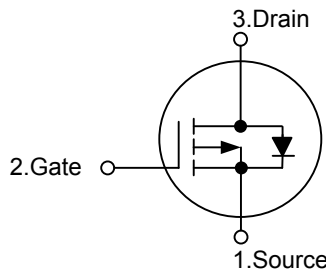
Y2.8A, 20V P-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

The UTC **UT2301** is P-channel enhancement mode power MOSFET, designed in serried ranks. With fast switching speed, low on-resistance, favorable stabilization.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

SYMBOL



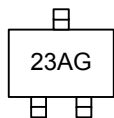
ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UT2301G-AE2-R	SOT-23-3	S	G	D	Tape Reel
UT2301G-AE3-R	SOT-23	S	G	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UT2301G-AE3-R</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) R: Tape Reel</p> <p>(2) AE2: SOT-23-3, AE3: SOT-23</p> <p>(3) G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 8	V
Continuous Drain Current	I_D	-2.8	A
Pulsed Drain Current (Note 1, 2)	I_{DM}	-10	A
Total Power Dissipation	P_D	1.14	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

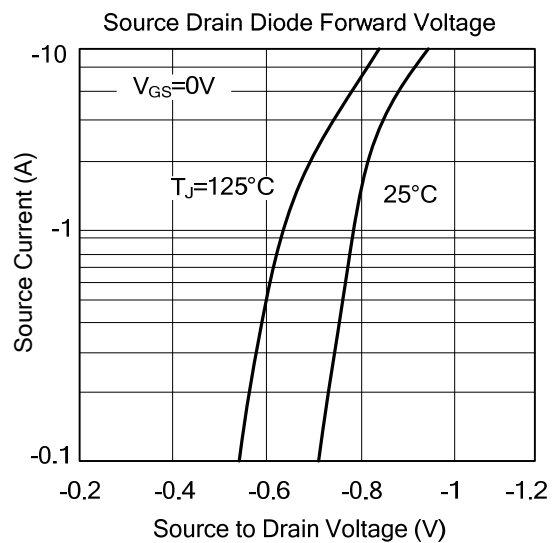
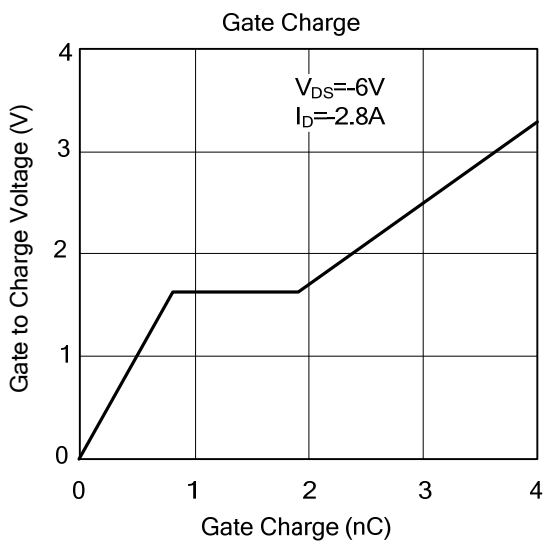
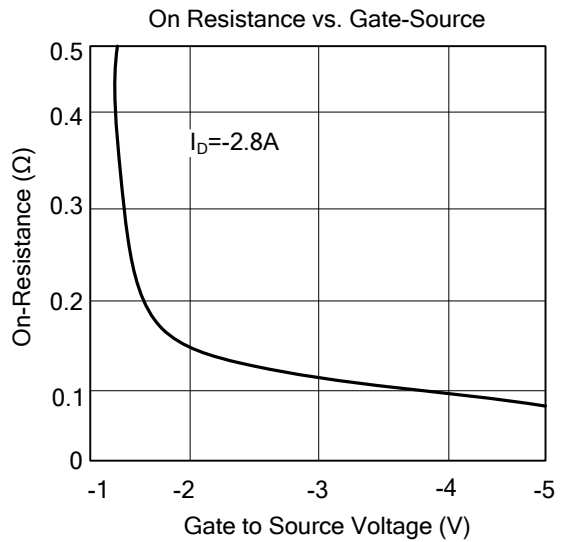
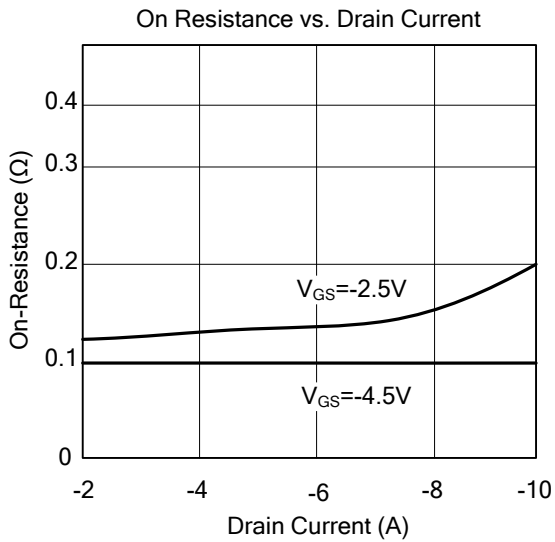
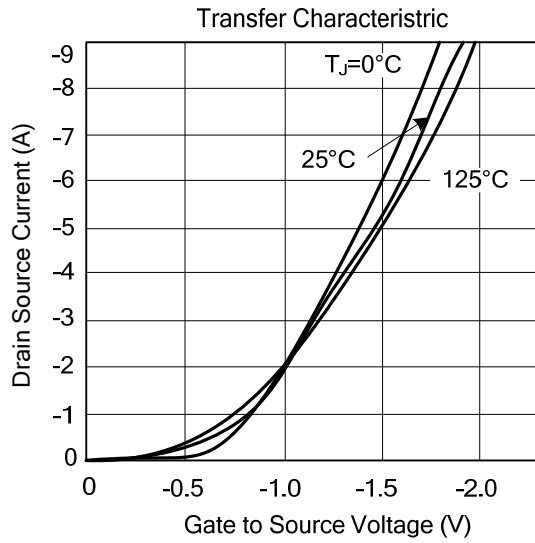
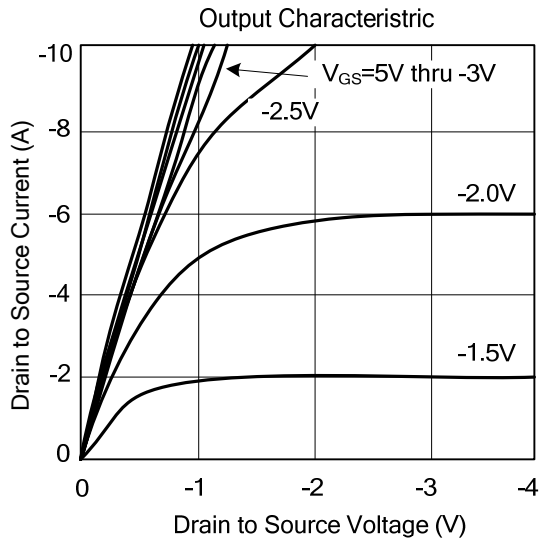
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient (Note 3)	θ_{JA}	110	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

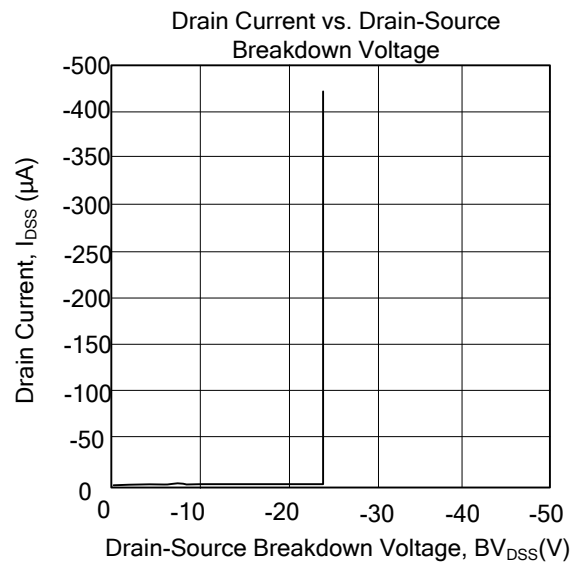
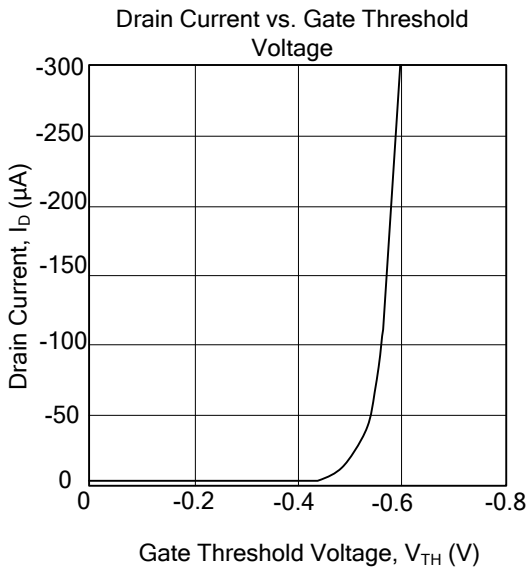
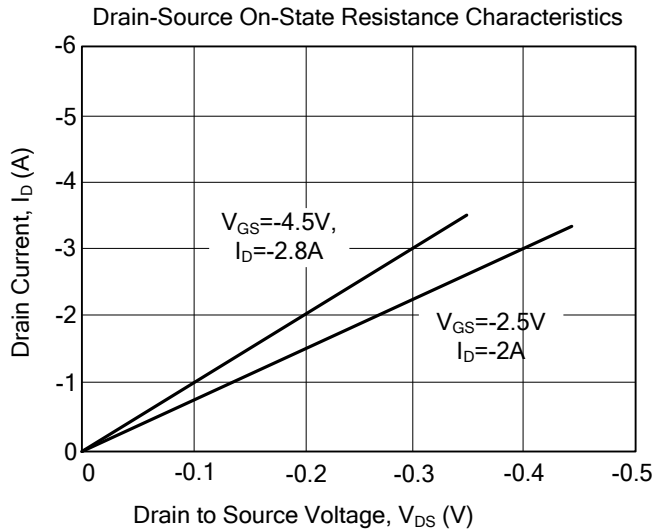
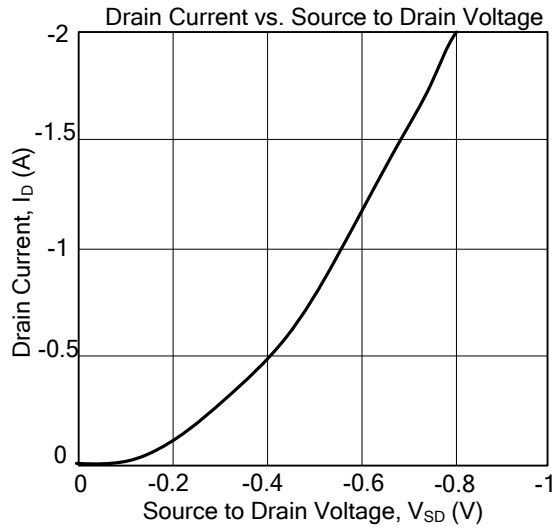
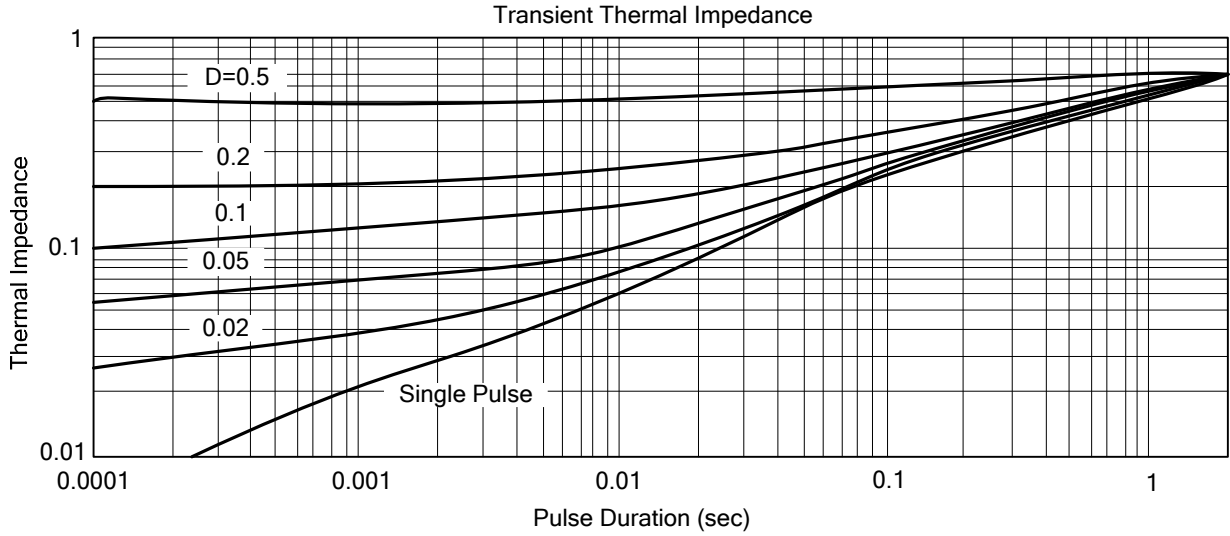
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-20			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.45			V
Static Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	$V_{GS}=-4.5\text{V}, I_D=-2.8\text{A}$		95	130	m Ω
		$V_{GS}=-2.5\text{V}, I_D=-2.0\text{A}$		122	190	m Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=-6\text{V}, f=1.0\text{MHz}$		447		pF
Output Capacitance	C_{OSS}			127		pF
Reverse Transfer Capacitance	C_{RSS}			80		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$	$V_{DS}=-6\text{V}, V_{GS}=-4.5\text{V}, I_D=-1\text{A}, R_G=6\Omega, R_L=6\Omega$		5	25	ns
Turn-ON Rise Time	t_R			19	60	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			95	110	ns
Turn-OFF Fall Time	t_F			65	80	ns
Total Gate Charge (Note 2)	Q_G	$V_{DS}=-6\text{V}, V_{GS}=-4.5\text{V}, I_D=-2.8\text{A}$		5.4	10	nC
Gate-Source Charge	Q_{GS}			0.8		nC
Gate-Drain Charge	Q_{GD}			1.1		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0\text{V}, I_S=-1.6\text{A}$		-0.8	-1.2	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				-1.6	A

- Notes: 1. Pulse width limited by $T_{J(MAX)}$
 2. Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
 3. Surface mounted on 1 in² copper pad of FR4 board

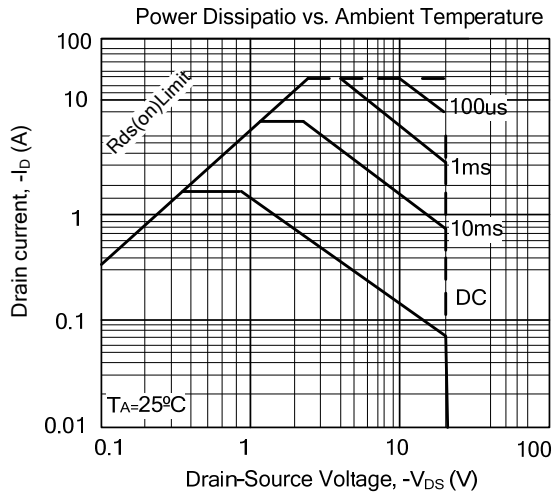
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)



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